



Features

- ✧ Glass passivated junction chip
- ✧ For surface mounted applications
- ✧ Low profile package
- ✧ Built-in strain relief
- ✧ Ideal for automated placement
- ✧ Easy pick and place
- ✧ Super fast recovery time for high efficiency
- ✧ Glass passivated chip junction
- ✧ High temperature soldering:
260°C/10 seconds at terminals
- ✧ Plastic material used carries Underwriters
Laboratory Classification 94V-0

Mechanical Data

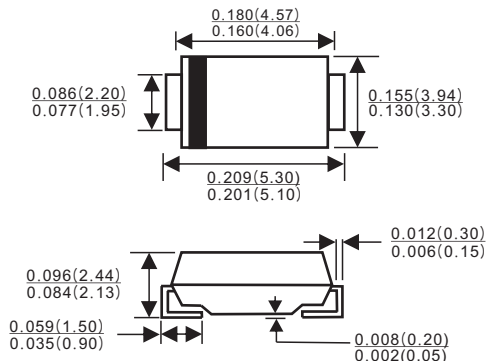
- ✧ Cases: Molded plastic
- ✧ Terminals: Pure tin plated, lead free.
- ✧ Polarity: Indicated by cathode band
- ✧ Weight: 0.21 gram

Marking Information



LGE: Lu Guang Electronic
XXXX: marking code (ES3A-ES3J)

SMB/DO-214AA



Dimensions in inches and(millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

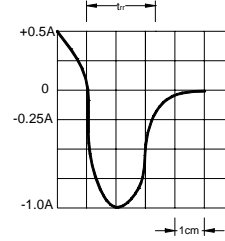
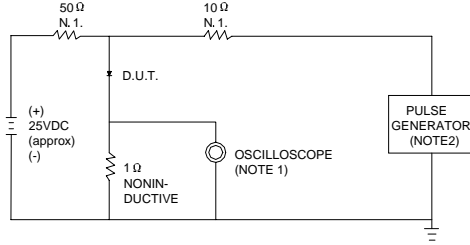
For capacitive load, derate current by 20%

Type Number	Symbol	ES 3A	ES 3B	ES 3C	ES 3D	ES 3F	ES 3G	ES 3H	ES 3J	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	500	600	V
Maximum RMS Voltage	V_{RMS}	35	70	105	140	210	280	350	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	500	600	V
Maximum Average Forward Rectified Current See Fig. 1	$I_{(AV)}$	3.0								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method) @ $T_L = 100^\circ\text{C}$	I_{FSM}	100								A
Maximum Instantaneous Forward Voltage @ 3.0A	V_F	0.95			1.3		1.7			V
Maximum DC Reverse Current @ $T_A = 25^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_A = 100^\circ\text{C}$	I_R	10				500				uA
Maximum Reverse Recovery Time (Note 1)	T_{rr}	35								nS
Typical Junction Capacitance (Note 2)	C_j	45				30				pF
Typical Thermal Resistance (Note 3)	$R_{\theta JA}$ $R_{\theta JL}$	47				12				$^\circ\text{C} / \text{W}$
Operating Temperature Range	T_J	-55 to +150								$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150								$^\circ\text{C}$

- Notes:
1. Reverse Recovery Test Conditions: $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$
 2. Measured at 1 MHz and Applied $V_R=4.0$ Volts
 3. Units Mounted on P.C.B. with 0.6" x 0.6"(16mm x 16mm) Copper Pad Areas

Ratings AND Characteristic Curves

FIG.1 -- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES:1.RISE TIME = 7ns MAX.INPUT IMPEDANCE = 1MΩ .22pF.
2.RISE TIME =10ns MAX.SOURCE IMPEDANCE=50 Ω .

SET TIME BASE FOR 20/30 ns/cm

FIG.2 -- TYPICAL FORWARD CHARACTERISTIC

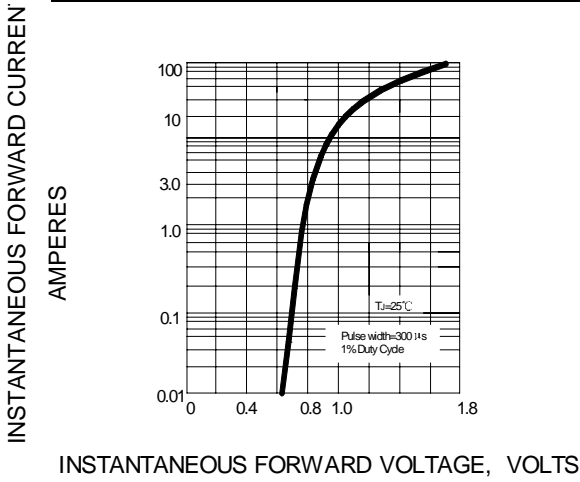


FIG.3 -- FORWARD DERATING CURVE

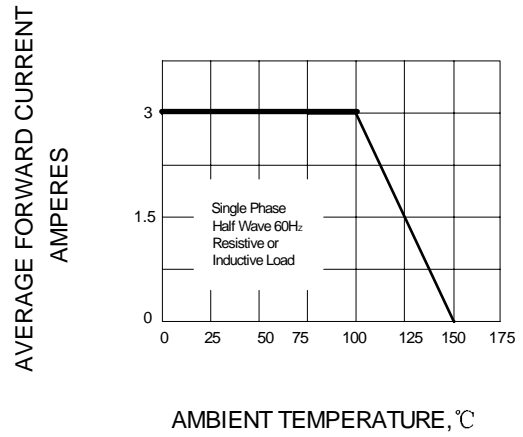


FIG.4 -- TYPICAL JUNCTION CAPACITANCE

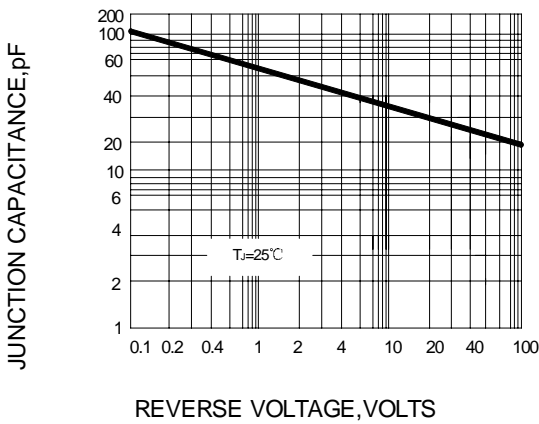
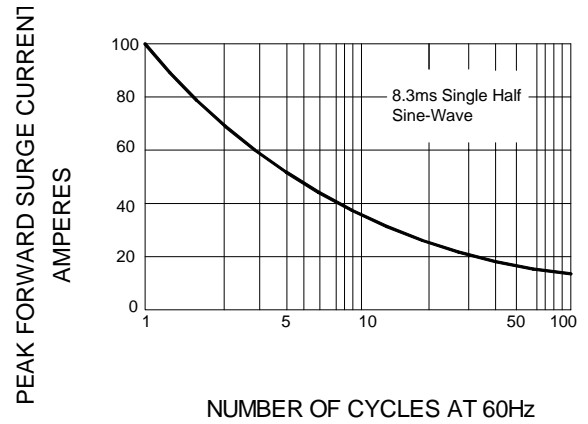


FIG.5 -- PEAK FORWARD SURGE CURRENT



PACKAGE	SPQ/PCS	CARTON SPQ/PCS	CARTON SIZE/CM	CARTON GW/KG	CARTON NW/KG
SMB	3000/REEL	48000	36X35.8X36.5	12.00	11.00